

**IN THE CLAIMS**

*Please amend the claims as follows:*

1. (Currently Amended) A semiconductor laser device, comprising:  
a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region formed of a gallium nitride-based crystal, wherein ~~an atmospheric gas inside the package contains oxygen~~ a rated output power of the semiconductor laser device is 30 mW or more, and an atmospheric gas inside the package is a mixture of oxygen and nitrogen, with an oxygen content of 20% or more.

2. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element has a dielectric oxide film formed on a laser emission surface thereof.

3. (Cancelled)

4. (Original) The semiconductor laser device of claim 1, wherein the semiconductor laser element emits light having a wavelength of 0.9  $\mu\text{m}$  or less.

5. (Currently Amended) ~~The semiconductor laser device of claim 1,~~ A semiconductor laser device, comprising:  
a semiconductor laser element arranged inside an airtight-sealed package, the semiconductor laser element having an active region formed of a gallium nitride-based crystal,  
wherein a rated output power of the semiconductor laser device is 30 mW or more, and

[[the]] an atmospheric gas inside the package is dry air.

6. (Cancelled)

7. (Cancelled)

8. (Cancelled)

9. (Previously Presented) The semiconductor laser device of claim 1, wherein the gallium nitride-based crystal is an AlGaN- or InGaN-based crystal.